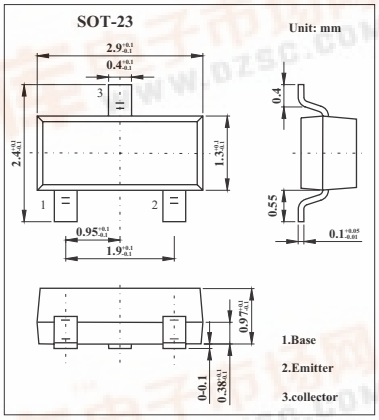
PNP Silicon Epitaxia Transistor

2SA1462



Features

- High speed,high voltage switching.
- High ft:fT=1800MHz TYP.
- Low Cob:Cob=2.0pF TYP.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-15	V
Collecto to emitter voltage	V_{CEO}	-15	V
Emitter to base voltage	V_{EBO}	-4.5	V
Collector current	I_C	-50	mA
Total power dissipation TA=25℃	P_T	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CES}	V_{CE} = -8.0V, R_{BE}=0			-100	nA
Emitter cutoff current	I_{EBO}	V_{EB} = -3.0V, I_C=0			-100	nA
DC current gain *	h_{FE}	V_{CE} = -1.0V , I_C = -10mA	50	80	150	
		V_{CE} = -1.0V , I_C = -1mA	30	70		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -10mA , I_B = -1.0mA		-0.09	-0.20	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = -10mA , I_B = -1.0mA		-0.98	-0.95	V
Gain bandwidth product	f_T	V_{CE} = -10V , I_E = 10mA	800	1800		MHz
Output capacitance	C_{ob}	V_{CB} = -5.0V , I_E = 0 , f = 1.0MHz		2.0	3.0	pF
Turnput Capacitance	t_{on}	I_C = -10mA , I_{B1} = I_{B1} = -1.0mA		9.0	20	ns
Storage Time	t_{stg}			16	40	ns
Turn-off Time	t_{off}			19	40	ns

* Pulse test: tp ≤ 350 μs; Duty Cycle≤2%

hFE Classification

Marking	Y33	Y34
hFE	50～100	75～150